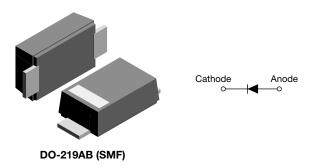
Vishay Semiconductors

www.vishay.com

Ultrafast Rectifier, 1 A FRED Pt®



PRODUCT SUMMARY					
Package	DO-219AB (SMF)				
I _{F(AV)}	1 A				
V _R	600 V				
V _F at I _F	0.83 V				
t _{rr}	55 ns				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Ultrafast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- For PCF CRM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 158 \ ^{\circ}{\rm C}^{(1)}$	1	٨			
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \text{ °C}, 6 \text{ ms} \text{ square pulse}$	30	A			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +175	°C			

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP.		MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-	
Forward voltage	V	I _F = 1 A	-	1.0	1.2	V
Forward voltage V _F		I _F = 1 A, T _J = 150 °C	-	0.83	1	
Devene la clus es comment	1	$V_{R} = V_{R}$ rated	-	-	3	
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	100	μA
Junction capacitance	CT	V _R = 600 V	-	5	-	pF

Revision: 22-Jan-16

1

Document Number: 95863

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



RoHS

COMPLIANT HALOGEN

FREE



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
			õs, V _R = 30 V	-	42	-	
Bayaraa raaayary tima	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	55	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	32	-	ns
		T _J = 125 °C	I _F = 1 A dI _F /dt = 500 A/μs V _R = 400 V	-	47	-	
Deck recovery current		T _J = 25 °C		-	4.8	-	
Peak recovery current	IRRM	T _J = 125 °C		-	6.8	-	A
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	77	-	nC
	Q _{rr}	T _J = 125 °C]	-	160	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to case	R _{thJC}	R _{thJC} Device mounted on PCB with 8 mm x 16 mm soldering lands		-	15	°C/W	
Thermal resistance, junction to ambient	R _{thJA} Device mounted on PCB with 2 mm x 3.5 mm soldering lands		-	-	130	°C/W	
Approvimente weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style DO-219AB (SMF)		M	NU		

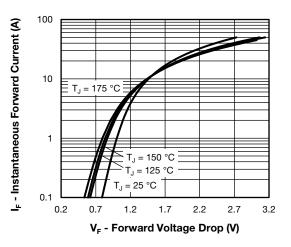


Fig. 1 - Typical Forward Voltage Drop Characteristics

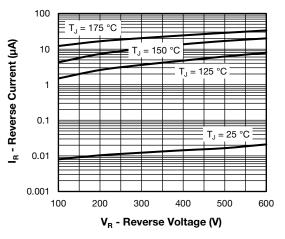


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay Semiconductors



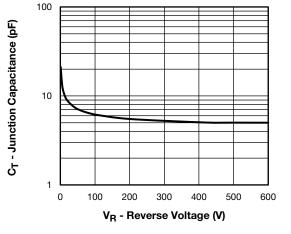


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

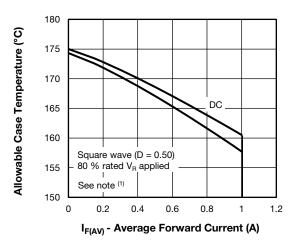


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

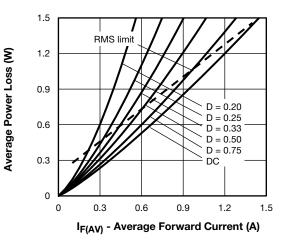


Fig. 5 - Forward Power Loss Characteristics

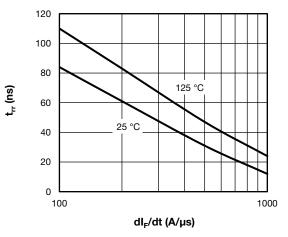


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

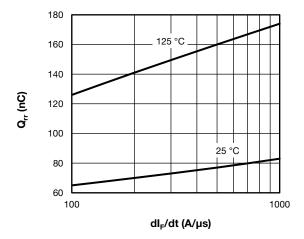


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/D) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated } \mbox{V}_{R} \end{array}$

Revision: 22-Jan-16

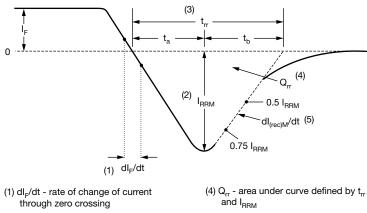
3

Document Number: 95863

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-1EFU06HM3

Vishay Semiconductors



(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

www.vishay.com

Device code	vs-	1	Е	F	U	06	н	МЗ
	1	2	3	4	5	6	7	8
	2 -	- Cur	rent rat	niconduo ing (1 = figuratio	1 A)	oduct		
	4 - 5 -	- F = - Pro	single c SMF pa cess typ	ackage be,				
	6 - 7 - 8 -	- Voli - H =	tage co AEC-Q	st recove de (06 = 101 qua jen-free,	600 V) alified	complia	ant, and	termin

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-1EFU06HM3/I	10 000	10 000	13"diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				
SPICE model	www.vishay.com/doc?95639				

Revision: 22-Jan-16

4

Document Number: 95863

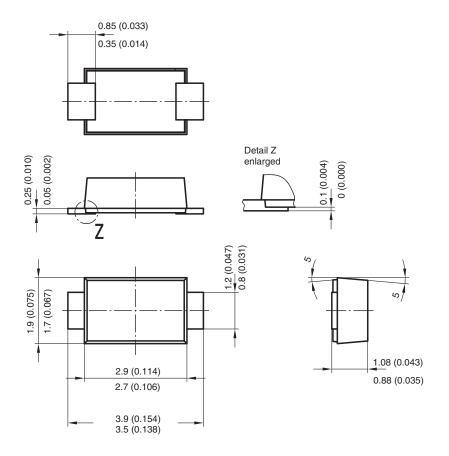
For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



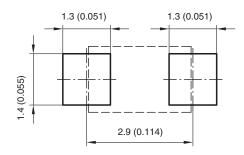
Vishay Semiconductors

DO-219AB (SMF)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.